	Hits	Search Text		Time stamp
mber		.1.	USPAT;	2003/02/19
imer	1207	(CMP or "chemical mechanical polishing"		14:51
		nishing or planarizing Of	IBM_TDB	
		planarization) and abrasive and pad and	1011_100	
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3	1416	/CMP or "chemical mechanical polishing	EPO; JPO;	16:21
		-ii-bing or hlaharizing OF	IBM TDB	
		and abrasive and pad and	TDM_TDD	
		and falumina or Silica of Cerra /		
		and (aluminum or al or titanium of ti		
		copper or Cu)	USPAT;	2003/02/19
1	4113	pad with abrasive	EPO; JPO;	16:22
		1	IBM TDB	
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5	920	((CMP or "chemical mechanical polishing"	EPO; JPO;	14:56
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	70	///CMP or "chemical mechanical polishing	USPAT;	14:57
	76	l line or planarizing of	EPO; JPO;	14:5/
		and ahrasive and pad and	IBM_TDB	
		1 3 man and (alumina or Silica of Colla /		
		1 1 /- 1 or al or fitanium of the		
	1	copper or Cu)) and (pad with abrasive))		!
		copper or cu) and (pad with and)	- C	
		and organic and oxidizer and organic and oxidizer	USPAT;	2003/02/19
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9	516	lishing or planarizing Of	EPO; JPO;	16:17
 		and anyasive and pad and	IBM_TDB	
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		same (aluminum of al of elemiconductor		
		copper or Cu)) and semiconductor	USPAT;	2003/02/19
10	110	(CMP or "chemical mechanical polishing"	EPO; JPO;	16:20
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2.3	173		EPO; JPO;	
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		mechanical polishing or polishing or	IBM_TDB	
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13	107	I . LLING COMO ANTASIVE	EPO; JPO;	
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